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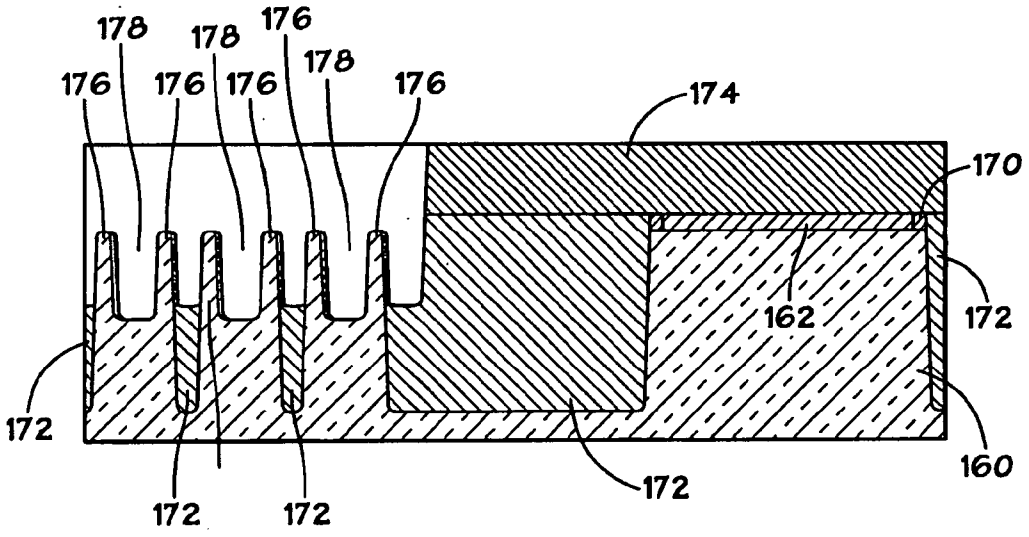
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(54) **Title:** SYSTEM AND METHOD FOR FABRICATING A FIN FIELD EFFECT TRANSISTOR



(57) **Abstract:** There is provided a system and method for fabricating a fin field effect transistor. More specifically, in one embodiment, there is provided a method comprising (134) depositing a layer of nitride (164) on a substrate (160), (136) applying a photolithographic mask on the layer of nitride (164) to define a location of a wall, (138) etching the layer of nitride (164) to create the wall, (140) removing the photolithographic mask, (142) depositing a spacer layer adjacent to the wall, (144) etching the spacer layer to create a spacer (170) adjacent to the wall, wherein the spacer (170) and the wall cover a first portion of the substrate (160), and etching a second portion of the substrate (160) not covered by the spacer (170) to create a trench (171).

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